

DERWENT- 1973-61838U

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WEEK:

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TITLE: Radiation sensitive device - using a semiconductor junction element for detection of conversion display of soft x-rays

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PRIORITY-DATA: 1970JP-0062976 (July 17, 1970)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
JP 73032940 B	N/A	000	N/A	

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ABSTRACTED-PUB-NO: JP 73032940B

BASIC-ABSTRACT:

A p type layer consisting of Cu₂S-Cu₂Se is formed on a n type semiconductor film consisting of a solid soln of CdS-CdSe doped with In to form a **heterojunction** element. A thin **film electrode** of Au is formed on the p type layer and a metal electrode of In is formed on the n type film. Two electrodes are connected by lead wires and to a variable d.c. power source and anammeter. A reverse bias voltage V_p is applied across the **heterojunction** element. When the **heterojunction** element is irradiated with soft x-rays, a.d.c. current I_p passing through the **heterojunction** element is detected with the d.c. ammeter.

TITLE- RADIATE SENSITIVE DEVICE SEMICONDUCTOR JUNCTION ELEMENT
TERMS: DETECT CONVERT DISPLAY SOFT RAY

DERWENT-CLASS: K08 L03 U12 U24 V05

CPI-CODES: K08-A; K08-X; L03-D04E; L03-H04C;